

REMARKS

Claim 29 has been amended twice and remains in this application. Claim 31 has been cancelled.

Examiner Marcos D. Pizarro is thanked for examining the present invention thoroughly.

Reconsideration of the rejection of claims 29-31 under 35 USC 102 as being anticipated by Sakakibara (US 5691560), is respectfully requested in view of the amended claims and for the reasons hereinafter given.

Claim 29 has been amended to incorporate the limitation cited in claim 31, and, accordingly, claim 31 has been cancelled. Thus, claim 29 now cites a lightly doped profile comprising phosphorous ions at a dosage level between about 1×10^{13} to 5×10^{13} atoms/cm² and a heavily doped profile comprising arsenic ions at a dosage level between about 1×10^{15} to 5×10^{15} atoms/cm².

It is respectfully submitted that claim 29 is different from the reference because the reference teaches high dosage levels of 1×10^{13} to 1×10^{15} for both the phosphorous



VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

Claim 29 has been amended as follows, and claim 30 cancelled:

29. (TWICE AMENDED) A stacked gate having a doubly diffused drain (DDD) comprising:

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a junction having a lightly doped profile, the profile comprising phosphorous ions at a dosage level between about

6 1×10^{13} to 5×10^{13} atoms/cm²; and

a surface region having a heavily doped profile, the

9 profile comprising arsenic ions at a dosage level between
about 1×10^{15} to 5×10^{15} atoms/cm².

Claim 31 has been cancelled.

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